





#### N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

### **Features**

- Low On-Resistance: R<sub>DS(ON)</sub>
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 2, 4 and 6)
- ESD Protected Up To 2kV

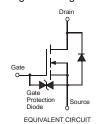
# **Mechanical Data**

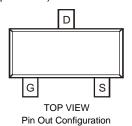
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)





SOT-23





**Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	60	V
Gate-Source Voltage		V <sub>GSS</sub>	±20	V
Drain Current (Note 1)	Continuous Pulsed (Note 3)		300 800	mA

## Thermal Characteristics @TA = 25°C unless otherwise specified

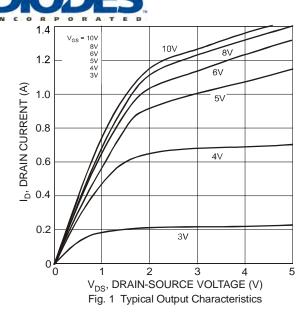
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	Pd	350	mW
Thermal Resistance, Junction to Ambient	$R_{ heta JA}$	357	°C/W
Operating and Storage Temperature Range	$T_{j,} T_{STG}$	-65 to +150	°C

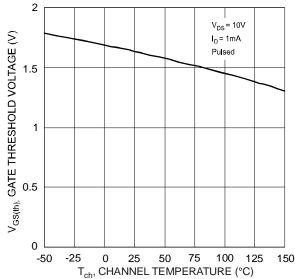
## **Electrical Characteristics** @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_{D} = 10\mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>		_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	1.6	2.5	V	$V_{DS} = 10V, I_{D} = 1mA$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	_	2.0		$V_{GS} = 10V, I_D = 0.5A$
Static Dialif-Source Off-Resistance		_		3.0		$V_{GS} = 5V, I_D = 0.05A$
Forward Transfer Admittance	Y <sub>fs</sub>	80	_	_	ms	$V_{DS} = 10V, I_D = 0.2A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>	_	_	50	pF	
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C <sub>rss</sub>			5.0	pF	

Notes:

- 1. Device mounted on FR-4 PCB.
- Device mounted on FR-4 FCB.
  No purposefully added lead. Halogen and Antimony Free.
- 3. Pulse width  $\leq 10 \mu S$ , Duty Cycle  $\leq 1\%$ .
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Short duration pulse test used to minimize self-heating effect.
- Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb<sub>2</sub>O<sub>3</sub> Fire Retardants.







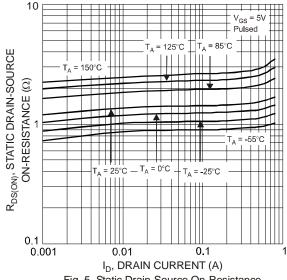
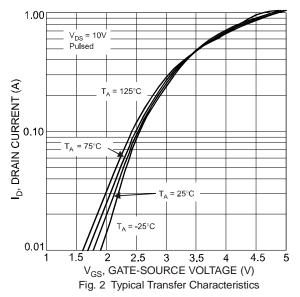


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



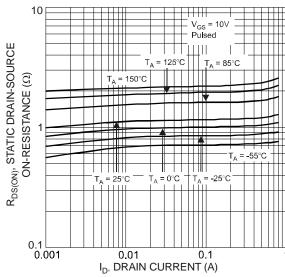


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

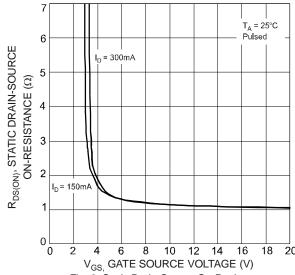
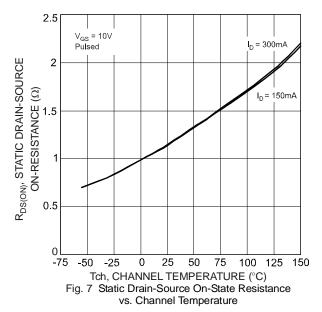
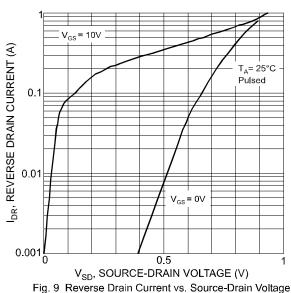
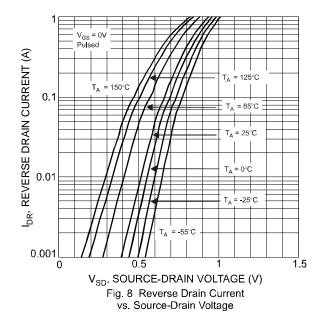


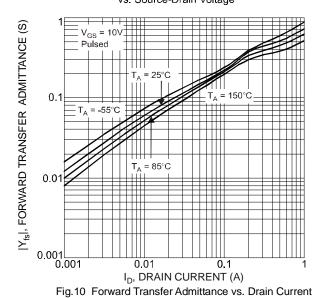
Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage









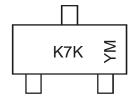


Ordering Information (Note 7)

Part Number	Case	Packaging
DMN601K-7	SOT-23	3000/Tape & Reel

Notes: 7. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



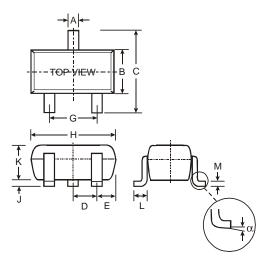
K7K = Product Type Marking Code YM = Date Code Marking Y = Year ex: S = 2005 M = Month ex: 9 = September

Date Code Key

zaio ocacito,												
Year	2005		2006	2007		2008	2009	)	2010	2011		2012
Code	S		T	U		V	W		Χ	Υ		Z
Month	Jan	Feb	Mar	Apr	May	/ Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

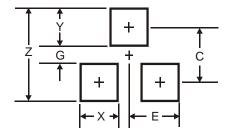


## **Package Outline Dimensions**



SOT-23					
Dim	Min	Max			
Α	0.37	0.51			
В	1.20	1.40			
С	2.30	2.50			
D	0.89 1.03				
E	0.45 0.60				
G	1.78 2.05				
Н	2.80	3.00			
J	<b>J</b> 0.013 0.10				
K	<b>K</b> 0.903 1.10				
L	<b>L</b> 0.45 0.61				
M	0.085	0.180			
α	0°	8°			
All Dir	All Dimensions in mm				

## **Suggested Pad Layout**



Dimensions	Value (in mm)
Z	3.4
G	0.7
X	0.9
Y	1.4
С	2.0
E	0.9

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